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U.S. PATENT & TRADEMARK OFFICE
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PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Leonard Forbes et al. Examiner: Theresa Doan
Serial No.: 09/883795 Group Art Unit: 2814
Filed: June 18, 2001 Docket: 303.355US4
Title: DEAPROM AND TRANSISTOR WITH GALLIUM NITRIDE OR GALLIUM
ALUMINUM NITRIDE GATE

INFORMATION DISCLOSURE STATEMENT

Mail Stop RCE
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

In compliance with the duty imposed by 37 C.F.R. § 1.56, and in accordance with 37 C.F.R. §§ 1.97 *et. seq.*, the enclosed materials are brought to the attention of the Examiner for consideration in connection with the above-identified patent application. Applicants respectfully request that this Information Disclosure Statement be entered and the documents listed on the attached Form 1449 be considered by the Examiner and made of record. Pursuant to the provisions of MPEP 609, Applicants request that a copy of the 1449 form, initialed as being considered by the Examiner, be returned to the Applicants with the next official communication.

Pursuant to 37 C.F.R. §1.97(b), it is believed that no fee or statement is required with the Information Disclosure Statement.

INFORMATION DISCLOSURE STATEMENT

Serial No.:09 883795

Filing Date: June 18, 2001

Title: DEAPROM AND TRANSISTOR WITH GALLIUM NITRIDE OR GALLIUM ALUMINUM NITRIDE GATE

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The Examiner is invited to contact the Applicants' Representative at the below-listed telephone number if there are any questions regarding this communication.

Respectfully submitted,

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Date 29 August 2003 By RE
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CERTIFICATE UNDER 37 CFR 1.8: The undersigned hereby certifies that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail, in an envelope addressed to: Mail Stop RCE, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on this 29th day of August, 2003.

Name

Amy Moriarty

Signature

Amy Moriarty

Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <small>(Use as many sheets as necessary)</small>		Complete if Known	
		Application Number	09/883795
		Filing Date	June 18, 2001
		First Named Inventor	Forbes, Leonard
		Group Art Unit	2814
		Examiner Name	Doan, Theresa
Sheet 1 of 1 <small>SEARCHED</small> <small>MAILED</small>		Attorney Docket No: 303.355US4	

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EXAMINER

DATE CONSIDERED